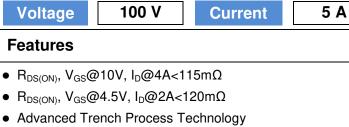
PΛN	ĴΪΤ
	SEMI CONDUCTOR

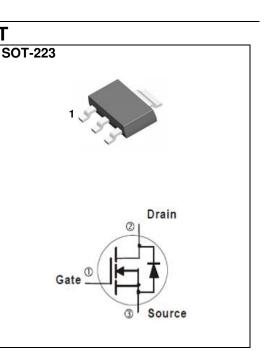
### 100V N-Channel Enhancement Mode MOSFET



- High density cell design for ultra low on-resistance
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

#### **Mechanical Data**

- Case : SOT-223 Package
- Terminals : Solderable per MIL-STD-750, Method 2026
- Approx. Weight : 0.043 ounces, 0.123 grams



#### **Maximum Ratings and Thermal Characteristics** ( $T_A=25^{\circ}C$ unless otherwise noted)

PARAMETEI	R	SYMBOL	LIMIT	UNITS
Drain-Source Voltage		V <sub>DS</sub>	100	Ň
Gate-Source Voltage		$V_{GS}$	<u>+</u> 20	V
Continuous Droin Current	T <sub>C</sub> =25°C	I <sub>D</sub>	5	
Continuous Drain Current	T <sub>C</sub> =100°C		3.1	Α
Pulsed Drain Current (Note 1)	T <sub>C</sub> =25°C	I <sub>DM</sub>	16	
Power Dissipation	T <sub>C</sub> =25°C	Po	5.2	14/
	T <sub>C</sub> =100°C		2.1	W
Continuous Drain Current (Note 4)	T <sub>A</sub> =25°C	I <sub>D</sub>	3.5	
	T <sub>A</sub> =70°C		2.8	Α
Power Dissipation	T <sub>A</sub> =25°C	PD	3.1	14/
	T <sub>A</sub> =70°C		2	W
Operating Junction and Storage Temperature Range		T <sub>J</sub> ,T <sub>STG</sub>	-55~150	°C
Typical Thermal Resistance (Note 4,5)	Junction to Case	$R_{ extsf{ heta}JC}$	24	°C 444
	Junction to Ambient	$R_{\theta JA}$	69.4	°C/W

Limited only By Maximum Junction Temperature



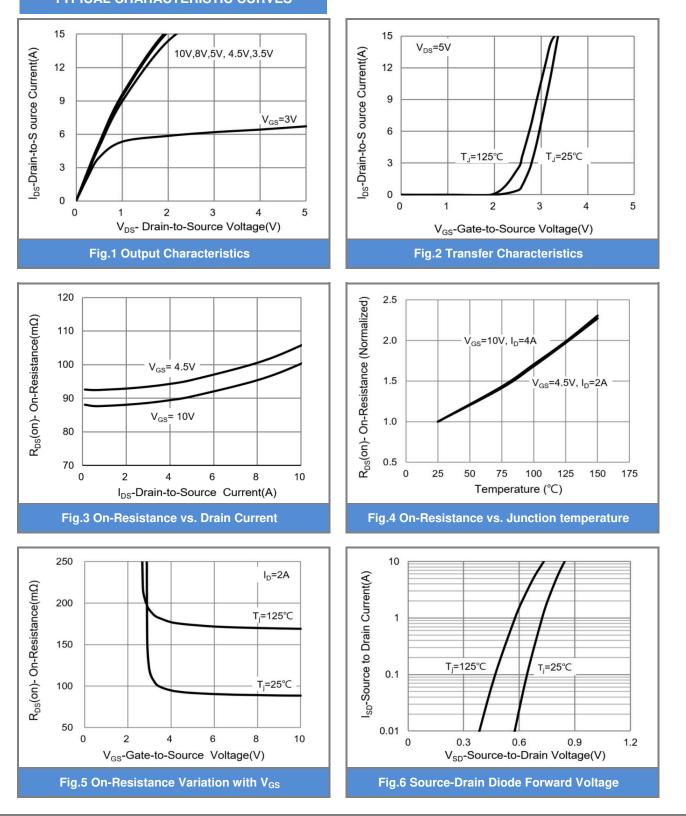
### Electrical Characteristics (T<sub>A</sub>=25°C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	$V_{GS}=0V,I_{D}=250uA$	100	-	-	
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS}=V_{GS}, I_{D}=250 \text{uA}$	1	1.76	2.5	V
		V <sub>GS</sub> =10V,I <sub>D</sub> =4A	-	92	115	mΩ
Drain-Source On-State Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =4.5V,I <sub>D</sub> =2A	-	95	120	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =100V,V <sub>GS</sub> =0V	-	-	1	uA
Gate-Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> = <u>+</u> 20V,V <sub>DS</sub> =0V	-	-	<u>+</u> 100	nA
Dynamic (Note 6)						
Total Gate Charge	Qg		-	20	-	nC
Gate-Source Charge	Q <sub>gs</sub>	$V_{DS}=50V, I_{D}=2A,$	-	3.2	-	
Gate-Drain Charge	Q <sub>gd</sub>	V <sub>GS</sub> =10V <sup>(Note 1,2)</sup>	-	3.6	-	
Input Capacitance	Ciss	V <sub>DS</sub> =25V, V <sub>GS</sub> =0V, f=1MHZ	-	1413	-	pF
Output Capacitance	Coss		-	60	-	
Reverse Transfer Capacitance	Crss		-	34	-	
Turn-On Delay Time	td <sub>(on)</sub>		-	18	-	
Turn-On Rise Time	tr	$V_{DD}$ =50V, I <sub>D</sub> =1A, $V_{GS}$ =10V, R <sub>G</sub> =3.3Ω <sup>(Note 1,2)</sup>	-	4.3	-	
Turn-Off Delay Time	td <sub>(off)</sub>		-	41	-	ns
Turn-Off Fall Time	t <sub>f</sub>	$H_{G}=3.3\Omega$	-	4.2	-	
Drain-Source Diode						
Maximum Continuous Drain-Source	I <sub>S</sub>		_	-	5	А
Diode Forward Current	'5		-	_	J	
Diode Forward Voltage	$V_{SD}$	I <sub>S</sub> =1A,V <sub>GS</sub> =0V	-	0.73	1	V

NOTES :

- 1. Pulse width <300us, Duty cycle <2%.
- 2. Essentially independent of operating temperature typical characteristics.
- 3. Repetitive rating, pulse width limited by junction temperature  $T_{J(MAX)}=150$  °C. Ratings are based on low frequency and duty cycles to keep initial  $T_J = 25$  °C.
- 4. The maximum current rating is package limited.
- 5.  $R_{\theta JA}$  is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch<sup>2</sup> with 2oz.square pad of copper.
- 6. Guaranteed by design, not subject to production testing.

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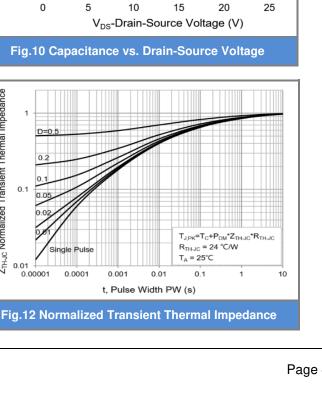
### TYPICAL CHARACTERISTIC CURVES

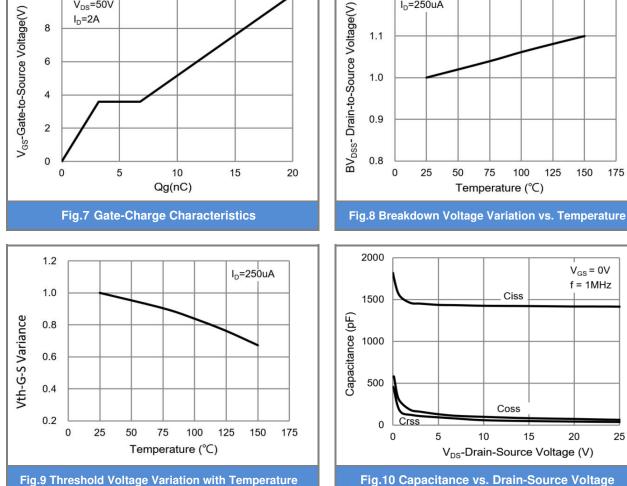
**PJW5N10A** 



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1.2

1.1

1.0

ZTH-JC Normalized Transient Thermal Impedance

10us

100us

1ms

10ms

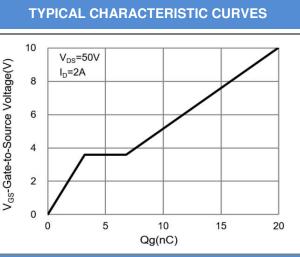
DC

100

1

0.1

I<sub>D</sub>=250uA



PANJ SEMI CONDUCTOR

**PJW5N10A** 



125

150

 $V_{GS} = 0V$ 

f = 1MHz

175

Drain-to-S ource Current - I<sub>D</sub> (A)

10

1

0.1

0.01

0.1

Operation this area is

1

Notes: 1. T<sub>J</sub>=150°C

2. T<sub>c</sub>=25°C

Fig.11 Maximum Safe Operating Area

3. Single pulse

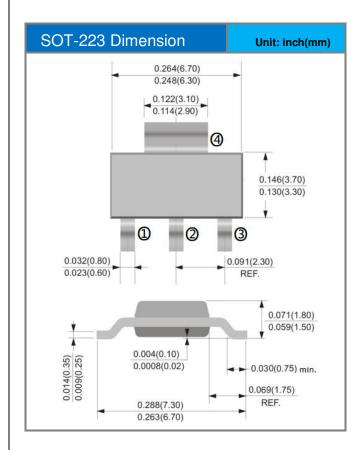
V<sub>DS</sub>-Drain-Source Voltage (V)

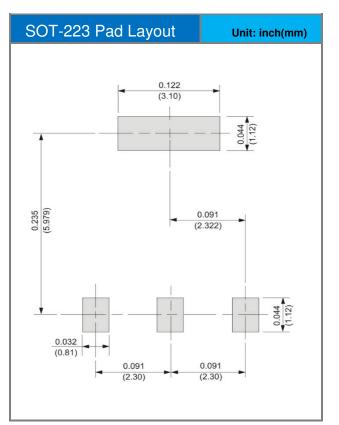
10

Limited by R<sub>DS(ON)</sub>



### Packaging Information & Mounting Pad Layout









#### Part No Packing Code Version

Part No Packing Code	Package Type	Packing Type	Marking	Version
PJW5N10A_R2_00001	SOT-223	2,500pcs / 13" reel	W5N10A	Halogen free



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